n-oxyg. silicon sensor, 300 um, 1.45e12/cm³, $V_{\rm bias}$ =1.5 $V_{\rm dep}$, $Q_{\rm in}$ =10 ke track 3 2.5 2 total induced charge [10 ke] 1.5 0.5 0 -0.5 -1.50.5 1.5 2 2.5 3 3.5 time [ns]